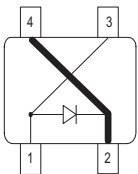


Silicon RF Switching Diode

- Designed for use in shunt configuration in high performance RF switches
- High shunt signal isolation
- Low shunt insertion loss
- Optimized for short - open transformation using $\lambda/4$ lines
- Pb-free (RoHS compliant) package


BAR81W


| Type | Package | Configuration | L_S (nH) | Marking |
|--------|---------|--------------------|------------|---------|
| BAR81W | SOT343 | single shunt-diode | 0.15* | BBs |

* series inductance chip to ground

Maximum Ratings at $T_A = 25^\circ\text{C}$, unless otherwise specified

| Parameter | Symbol | Value | Unit |
|---|------------------|-------------|------|
| Diode reverse voltage | V_R | 30 | V |
| Forward current | I_F | 100 | mA |
| Total power dissipation $T_S \leq 138^\circ\text{C}$ | P_{tot} | 100 | mW |
| Junction temperature | T_j | 150 | °C |
| Operating temperature range | T_{op} | -55 ... 125 | |
| Storage temperature | T_{stg} | -55 ... 150 | |

Thermal Resistance

| Parameter | Symbol | Value | Unit |
|--|-------------------|------------|------|
| Junction - soldering point ¹⁾ | R_{thJS} | ≤ 120 | K/W |

¹⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

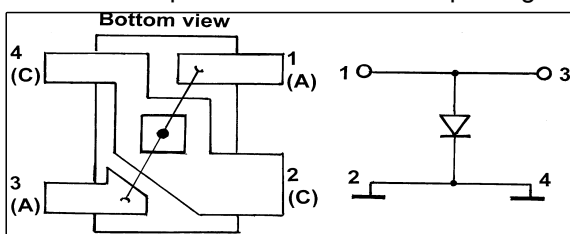
| Parameter | Symbol | Values | | | Unit |
|--|--------|--------|------|------|------|
| | | min. | typ. | max. | |
| DC Characteristics | | | | | |
| Reverse current $V_R = 20\text{ V}$ | I_R | - | - | 20 | nA |
| Forward voltage $I_F = 100\text{ mA}$ | V_F | - | 0.93 | 1 | V |

AC Characteristics

| | | | | | |
|--|-------------|---|-----|---|---------------|
| Diode capacitance $V_R = 1\text{ V}, f = 1\text{ MHz}$ $V_R = 3\text{ V}, f = 1\text{ MHz}$ | C_T | - | 0.6 | 1 | pF |
| Forward resistance $I_F = 5\text{ mA}, f = 100\text{ MHz}$ | r_f | - | 0.7 | 1 | Ω |
| Charge carrier life time $I_F = 10\text{ mA}, I_R = 6\text{ mA}$, measured at $I_R = 3\text{ mA}$, $R_L = 100\ \Omega$ | τ_{rr} | - | 80 | - | ns |
| I-region width | W_I | - | 3.5 | - | μm |
| Shunt Insertion loss ¹⁾ $I_F = 10\text{ mA}, f = 1.89\text{ GHz}$ | I_L | - | 30 | - | dB |
| Shunt isolation ¹⁾ $V_R = 3\text{ V}, f = 1.89\text{ GHz}$ | I_{SO} | - | 0.7 | - | |

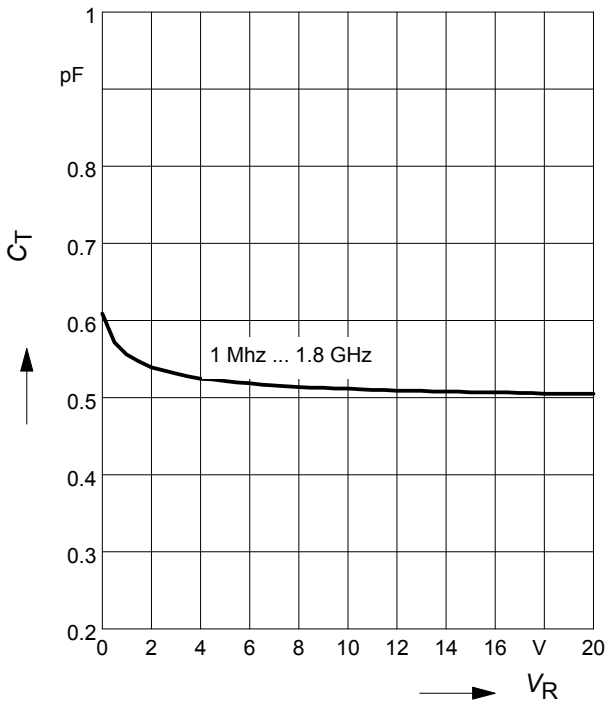
Configuration of the shunt-diode

- A perfect ground is essential for optimum isolation
- The anode pins should be used as passage for RF


¹For more information please refer to Application Note 049.

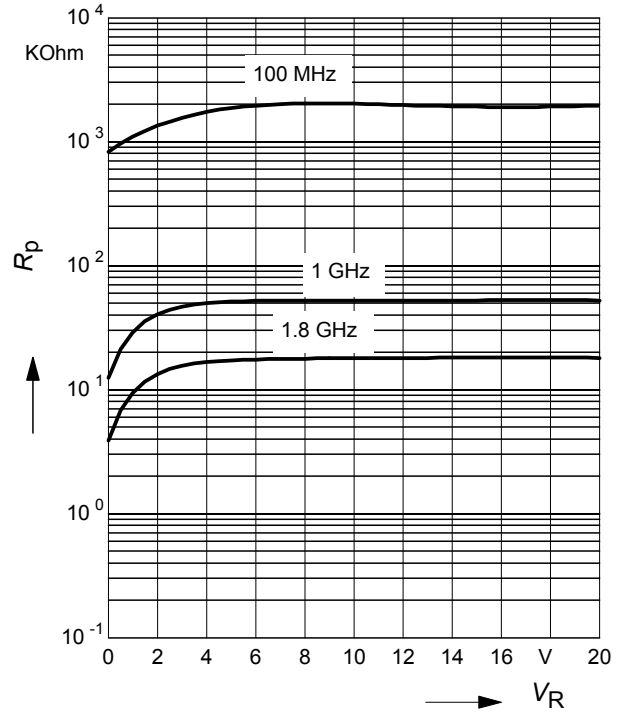
Diode capacitance $C_T = f(V_R)$

$f =$ Parameter



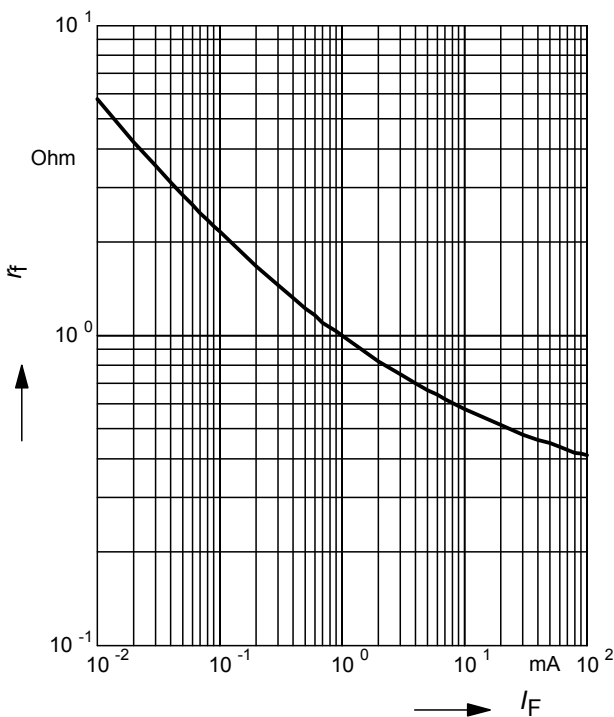
Reverse parallel resistance $R_P = f(V_R)$

$f =$ Parameter



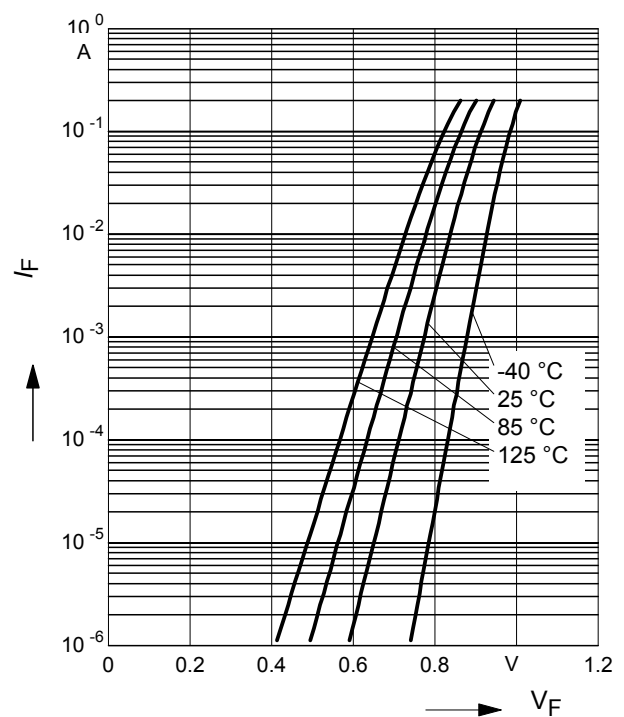
Forward resistance $r_f = f(I_F)$

$f = 100\text{MHz}$



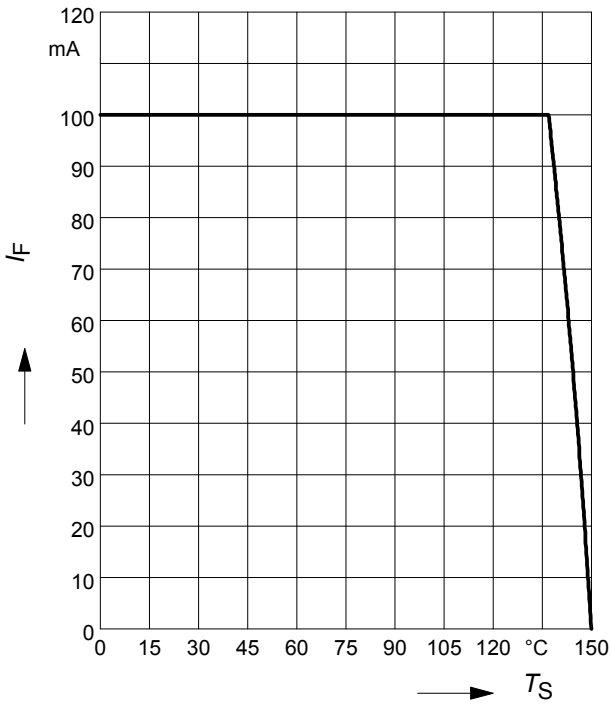
Forward current $I_F = f(V_F)$

$T_A =$ Parameter



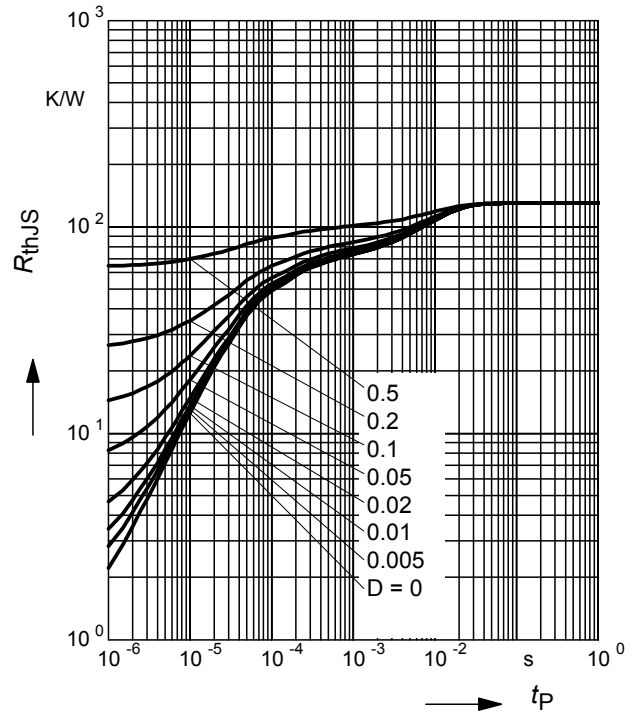
Forward current $I_F = f(T_S)$

BAR81W



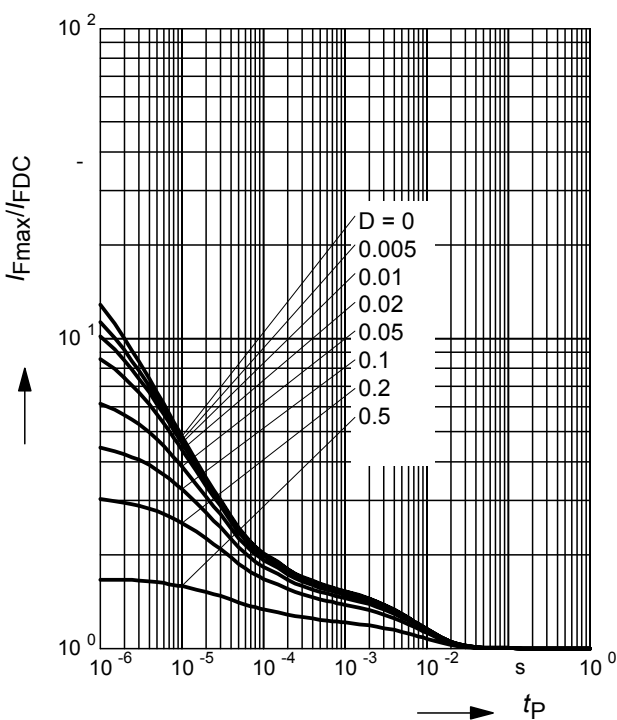
Permissible Puls Load $R_{thJS} = f(t_p)$

BAR81W

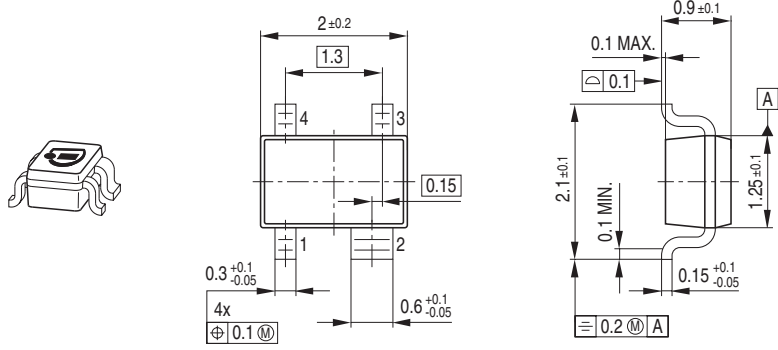


Permissible Pulse Load

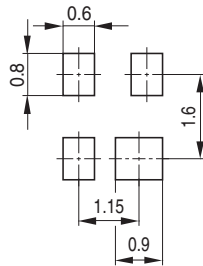
$I_{Fmax} / I_{FDC} = f(t_p)$ BAR81W



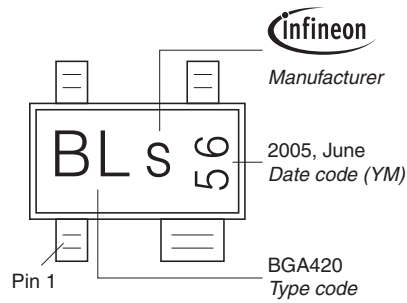
Package Outline



Foot Print

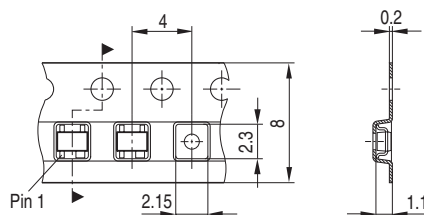


Marking Layout (Example)



Standard Packing

Reel \varnothing 180 mm = 3.000 Pieces/Reel
 Reel \varnothing 330 mm = 10.000 Pieces/Reel



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